



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

Device	BV _{DSS}	Rds(on) max	ID MAX TA = +25°C
		$61m\Omega @ V_{GS} = -4.5V$	-3.8A
P-Channel	-12V	81mΩ @ V _{GS} = -2.5V	-3.3A
		115mΩ @ V _{GS} = -1.8V	-2.8A

Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

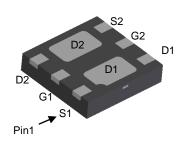
Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

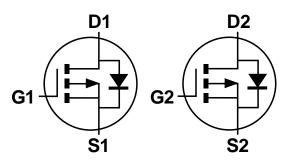
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁶⁴
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type B)



Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP1046UFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel		
DMP1046UFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



P6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Ι		J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



P6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Date Code Key												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5		0	1	2	3	4	5	6	7	8	9
Week	Week 1-26				27-	-52		53				
Code	A-Z			A-Z a-z				Z				
Internal Code	Sun Mon			de Sun Mon Tue Wed Thu					Fri		Sat	
Code	Т		U		V	V	V	Χ		Υ		Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	-12	V	
Gate-Source Voltage		V_{GSS}	±8	V	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lσ	-3.8 -3.0	А
Continuous Diain Current (Note 5) VGS = -4.5V	$t < 5s$ $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		lο	-5.0 -4.0	А
Maximum Continuous Body Diode Forward Curre	nt (Note 5)		Is	-1	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	l%)	I _{DM}	-15	Α	
Avalanche Current (L = 0.1mH)		I _{AS}	-12	Α	
Avalanche Energy (L = 0.1mH)			Eas	8	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	Steady State	D-	1.4	W	
Total Fower Dissipation (Note 3)	t < 5s	PD	2.2	VV	
Thermal Begistance, Junction to Ambient (Note 5)	Steady State	D	92		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	R _θ JA	55	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R _θ JC	20			
Operating and Storage Temperature Range		TJ, TSTG	-55 to 150	°C	

Note: 5. Device mounted on 1" × 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

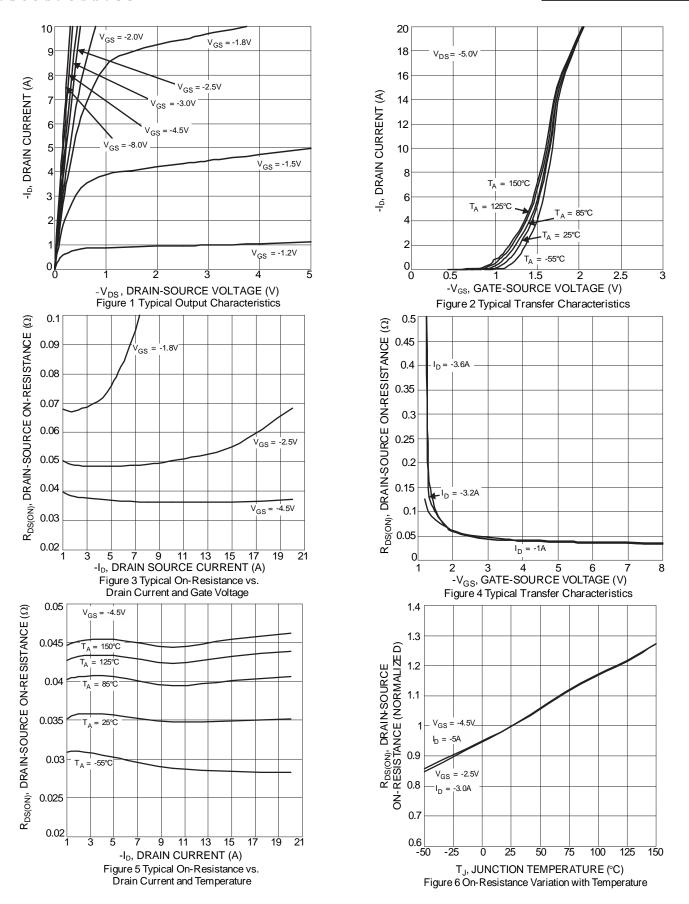
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1.0	μΑ	V _{DS} = -12V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	Vgs(TH)	-0.4		-1	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
			37	61		$V_{GS} = -4.5V$, $I_{D} = -3.6A$
Static Drain-Source On-Resistance	R _{DS(ON)}		47	81	$m\Omega$	$V_{GS} = -2.5V$, $I_D = -3.2A$
	- (- ')		63	115		$V_{GS} = -1.8V, I_{D} = -1.0A$
Diode Forward Voltage	V_{SD}	_	-0.65	-1.2	V	$V_{GS} = 0V, I_{S} = -4.5A$
DYNAMIC CHARACTERISTICS (Note 7)	•			•		
Input Capacitance	Ciss		915		рF)/ O)/)/
Output Capacitance	Coss	_	225	_	pF	V _{DS} = -6V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss		183	_	pF	1 = 1.0lvii iz
Gate Resistance	Rg		56.9	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (VGS = -4.5V)	0		10.7	_	nC	
Total Gate Charge (V _{GS} = -8V)	Qg	_	17.9	_	nC	V _{DS} = -6V. I _D = -4.3A
Gate-Source Charge	Qgs		1.7	_	nC	$V_{DS} = -6V, I_{D} = -4.3A$
Gate-Drain Charge	Qgd	_	3.0	_	nC	
Turn-On Delay Time	td(ON)	_	5.7	_	ns	
Turn-On Rise Time	t _R		11.5	_	ns	$V_{DD} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	tD(OFF)		27.8	_	ns	$R_L = 1.6\Omega$, $R_G = 1\Omega$
Turn-Off Fall Time	t _F		26.4	_	ns]

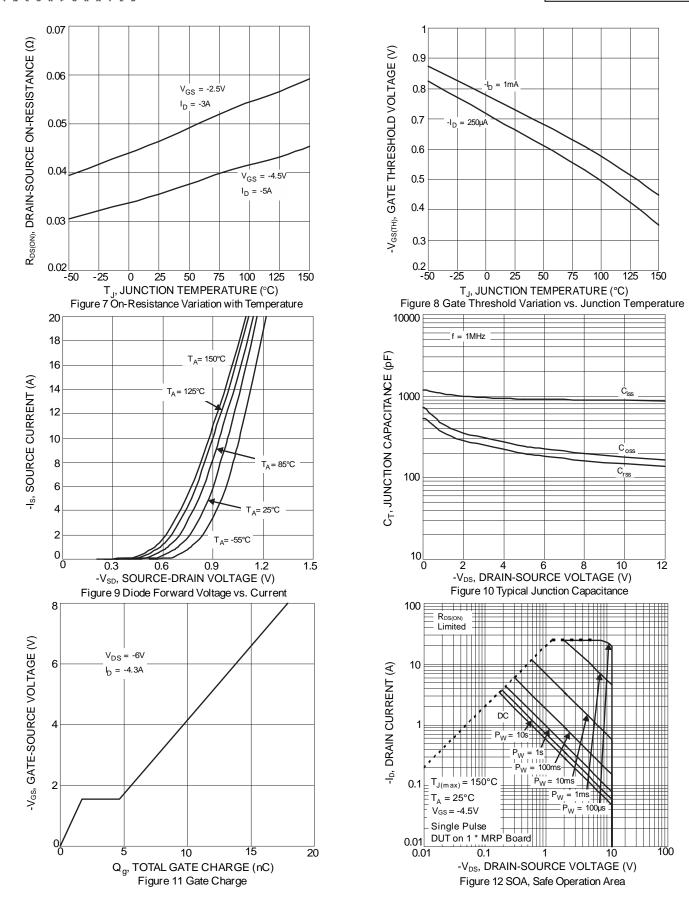
Notes: 6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to product testing.

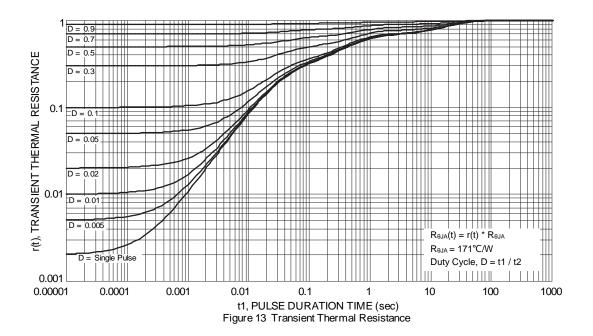










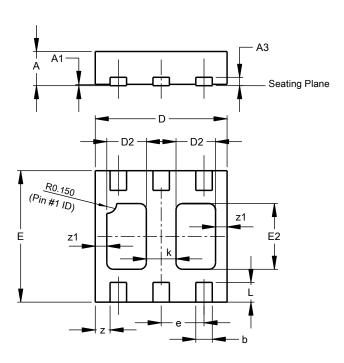




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

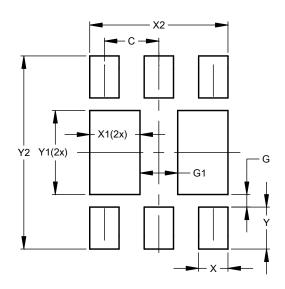


U-DFN2020-6 Type B						
Dim	Min	Тур				
Α	0.545	0.605	0.575			
A 1	0.00	0.05	0.02			
A3	-	-	0.13			
b	0.20	0.30	0.25			
D	1.95	2.075	2.00			
D2	0.50	0.70	0.60			
е	-	-	0.65			
Е	1.95	2.075	2.00			
E2	0.90	1.10	1.00			
k	-	-	0.45			
L	0.25	0.35	0.30			
Z	-	-	0.225			
z1	-	-	0.175			
All I	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)				
С	0.650				
G	0.150				
G1	0.450				
Х	0.350				
X1	0.600				
X2	1.650				
Y	0.500				
Y1	1.000				
Y2	2 300				



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com